IN THE CLAIMS

Please amend the claims as follows:

Claims 1-11 (Canceled).

Claim 12 (Currently Amended): ~~The~~ A method of manufacturing a semiconductor device ~~according to claim 11~~ comprising:

forming a first gate electrode on a first semiconductor layer in a first region of a semiconductor substrate, and a second gate electrode on a second semiconductor layer in a second region of the semiconductor substrate;

forming a first diffusion layer in said first semiconductor layer using said first gate electrode as a mask, and a second diffusion layer in said second semiconductor layer using said second gate electrode as a mask; and

selectively forming an epitaxial layer only on said first diffusion layer,

wherein said first region is an SOI region, and said second region is a bulk region.

Claim 13 (Currently Amended): ~~The~~ A method of manufacturing a semiconductor device ~~according to claim 11~~ comprising:

forming a first gate electrode on a first semiconductor layer in a first region of a semiconductor substrate, and a second gate electrode on a second semiconductor layer in a second region of the semiconductor substrate;

forming a first diffusion layer in said first semiconductor layer using said first gate electrode as a mask, and a second diffusion layer in said second semiconductor layer using said second gate electrode as a mask; and

selectively forming an epitaxial layer only on said first diffusion layer,

wherein said selective forming of the epitaxial layer includes:

forming an oxide layer on the surface of said second diffusion layer in said second region by emitting O_2 plasma with only said first region being masked; and

subsequently forming said epitaxial layer by epitaxial growth on said first diffusion layer.

Claim 14 (Currently Amended): ~~The~~ A method of manufacturing a semiconductor device ~~according to claim 11, further including~~ comprising:

forming a first gate electrode on a first semiconductor layer in a first region of a semiconductor substrate, and a second gate electrode on a second semiconductor layer in a second region of the semiconductor substrate;

forming a first diffusion layer in said first semiconductor layer using said first gate electrode as a mask, and a second diffusion layer in said second semiconductor layer using said second gate electrode as a mask;

implanting carbon into said first and second diffusion layers ~~before forming said epitaxial layer~~, and

selectively forming an epitaxial layer only on said first diffusion layer,

wherein said selective forming of the epitaxial layer includes:

forming an oxide layer on the surface of said first diffusion layer in said first region by emitting O_2 plasma with only said second region being masked;

removing the mask, and then removing said oxide layer; and

subsequently forming said epitaxial layer by epitaxial growth on said first diffusion layer.

Claim 15 (Original) The method of manufacturing a semiconductor device according to claim 14, wherein said implanting carbon is performed by forming first and second gate sidewalls at side portions of said first and second gate electrodes through the RIE method using carbon gas as an active gas.

Claims 16-18 (Canceled).